S18-0425-Rev. B, 23-Apr-18

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Vishay Siliconix

DG2012E

Powered-off Protection, 1 Ω , 1.8 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer)

DESCRIPTION

The DG2012E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of 1 Ω at a 5 V power supply, low power consumption, and fast switching speeds.

The DG2012E can handle both analog and digital signals and permits signals with amplitudes of up to V+ to be transmitted in either direction. Its control logic inputs can go over V+ up to 5.5 V. It features break before make switching performance. Its -3 dB bandwidth is typically 160 MHz.

A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to V+ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).

Operation temperature is specified from -40 °C to +85 °C. The DG2012E is available in SC-70-6L package.

FEATURES

- Low switch on-resistance (1 Ω)
- 1.65 V to 5.5 V single supply operation
- Isolation in powered-off mode
- Control logic inputs can go over V+
- Low charge injection (5 pC)
- · Low total harmonic distortion
- · Break before make switching
- Latch-up performance exceeds 300 mA per JESD 78
- ESD tested
 - 7000 V human body model (JS-001)
 - 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

Note

This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

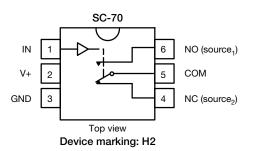
- Smartphones and tablets
- Consumer and computing
- Portable instrumentation

Pin 1

Device marking: H2XXX XXX = date / lot traceability code

Medical equipment

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE					
LOGIC	NC	NO			
0	On	Off			
1	Off	On			

ORDERING INFORMATION					
TEMP. RANGE	PACKAGE	PACKAGE PART NUMBER			
-40 °C to +85 °C	SC-70-6	DG2012EDL-T1-GE3			

H2XXX







ABSOLUTE MAXIMUM BATINGS

ADJULUTE MAAIMUMI KATI	143		
PARAMETER		LIMIT	UNIT
V+, COM, NC, NO, IN reference to GND		-0.3 to 6	V
Continuous current (NO, NC, and COM p	pins)	± 100	mA
Peak current (pulsed at 1 ms, 10 % duty	± 300		
Storage temperature (D suffix)		-65 to +150	°C
Power dissipation (packages) ^a	6-pin SO-70 ^b	250	mW
ESD / HBM	JS-001	7000	V
ESD / CDM	JS-002	1000	v
Latch up	Per JESD78 with 1.5 x voltage clamp	300	mA

Notes

a. All leads welded or soldered to PC board b. Derate 3.1 mW/°C above 70 $^\circ\text{C}$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+	= 5 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^a	LIMITS -40 °C to +85 °C			UNIT
		V+ = 5 V, \pm 10 %, V _{IN} = 0.8 V or 2.4 V $^{\rm e}$		MIN. ^b	۲YP. ۵	MAX. ^b	
Analog Switch					1	1	
Analog signal range ^d	V _{NO} , V _{NC} V _{COM}		Full	0	-	V+	V
On-resistance	R _{ON}	V+ = 4.5 V, V _{COM} = 0.5 V / 2.5 V, I _{NO} , I _{NC} = 10 mA	Room Full ^d	-	1	1.6 2	
R _{ON} flatness ^d	R _{ON} flatness	V+ = 4.5 V,	Room	-	0.2	0.5	Ω
R _{ON} match ^d	ΔR_{ON}	$V_{COM} = 0$ V to V+, I_{NO} , $I_{NC} = 10$ mA	Room	-	-	0.3	
	I _{NO(off)}		Room	-5	-	5	
	I _{NC(off)}	V + = 5 V	Full	-20	-	20	
Switch off leakage current f		V _{NO} , V _{NC} = 0.5 V / 4.5 V, V _{COM} = 4.5 V / 0.5 V	Room	-5	-	5	1.
	ICOM(off)		Full ^d	-20	-	20	nA
		V+ = 5 V,	Room	-5	-	5	
Channel-on leakage current f	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 0.5 V / 4.5 V$	Full ^d	-20	-	20	
Power down leakage	I _{COM(PD)}	$V_{+} = 0 V, V_{COM} = 4.5 V, V_{IN} = GND$	Full ^d	-1	-	1	μA
Digital Control					•	•	
Input high voltage	V _{INH}		Full	2.4	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.8	v
Input capacitance ^d	C _{IN}		Full	-	3	-	pF
Input current ^f	I _{INL} or I _{INH}	$V_{IN} = 0 V \text{ or } V+$	Full	-1	-	1	μA
Dynamic Characteristics					•	•	
Turn-on time ^d			Room	-	15	32	
Turn-on time "	t _{ON}	V_{NO} or V_{NC} = 3 V, R _L = 300 Ω , C _L = 35 pF	Full ^d	-	-	35	ns
Turn-off time ^d			Room	-	7	28	
Turn-off time a	t _{OFF}		Full ^d	-	-	30	
Break-before-make time d	t _d		Room	1	5	-	
Charge injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room	-	8	-	рС
Off-isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, f = 1 MHz	Room	-	-63	-	
Crosstalk ^d	X _{TALK}		Room	-	-63	-	dB
N_O , N_C off capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	16	-	рF
Channel-on capacitance d	C _{ON}	- IIV	Room	-	52	-	•
Power Supply							
Power supply current	l+	V _{IN} = 0 V or V+	Full	-	0.0003	1	μA

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DG2012E

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SPECIFICATIONS (V+ = 3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 3 V, \pm 10 %, V _{IN} = 0.4 V or 1.4 V e	TEMP. ^a	LIMITS -40 °C to 85 °C			UNIT
				MIN. ^b	TYP. °	MAX. ^b	
Analog Switch							
Analog signal range ^d	V _{NO} , V _{NC} V _{COM}		Full	0	-	V+	V
On-resistance	R _{ON}	V+ = 2.7 V, V _{COM} = 0.2 V / 1.5 V, I _{NO} I _{NC} = 10 mA	Room Full ^d	-	1.4 -	2.5 3	
R _{ON} flatness ^d	R _{ON} flatness	V + = 2.7 V,	Room	-	0.6	0.9	Ω
R _{ON} match ^d	ΔR_{ON}	$V_{COM} = 0$ V to V+, I_{NO} , $I_{NC} = 10$ mA	Room	-	-	0.3	
	I _{NO(off)}		Room	-5	-	5	
Quitch off lookage ourset f	I _{NC(off)}	V+ = 3.3 V	Full	-15	-	15	
Switch off leakage current f		V_{NO} , V_{NC} = 1 V / 3 V, V_{COM} = 3 V / 1 V	Room	-5	-	5	nA
	ICOM(off)		Full ^d	-15	-	15	
Observation lastrana summart f		$V_{\rm H} = 3.3 \text{ V},$ $V_{\rm NO}, V_{\rm NC} = V_{\rm COM} = 1 \text{ V} / 3 \text{ V}$	Room	-5	-	5	
Channel-on leakage current f	I _{COM(on)}		Full ^d	-15	-	15	
Digital Control							
Input high voltage	V _{INH}		Full	1.4	-	-	v
Input low voltage	V _{INL}		Full	-	-	0.4	v
Input capacitance d	C _{IN}		Full	-	3	-	pF
Input current ^f	$I_{\rm INL}$ or $I_{\rm INH}$	$V_{IN} = 0 V \text{ or } V+$	Full	-1	-	1	μA
Dynamic Characteristics							
Turn-on time ^d	tau		Room	-	21	42	
rum-on time	t _{ON}		Full ^d	-	-	47]
Turn-off time ^d	t	V_{NO} or $V_{NC} = 2 V$, $R_L = 300 \Omega$, $C_L = 35 pF$	Room	-	16	32	ns
	t _{OFF}		Full ^d	-	-	35	-
Break-before-make time ^d	t _d		Room	1	7	-	
Charge injection ^d	Q _{INJ}	${\sf C}_{\sf L}$ = 1 nF, ${\sf V}_{\sf GEN}$ = 0 V, ${\sf R}_{\sf GEN}$ = 0 Ω	Room	-	6	-	рС
Off-isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-63	-	dB
Crosstalk ^d	X _{TALK}	$m_{L} = 50.52, O_{L} = 5.000, i = 1.00002$	Room	-	-63	-	uD
Bandwidth ^d	BW		Room	-	160	-	MHz
N_O , N_C off capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	16	-	pF
Channel-on capacitance ^d	C _{ON}		Room	-	52	-	
Power Supply							
Power supply current	l+	V _{IN} = 0 V or V+	Full	-	0.00002	1	μA



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DG2012E

Vishay Siliconix

SPECIFICATIONS (V+	= 2 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^a	LIMITS -40 °C to +85 °C			UNIT
		V+ = 2 V, \pm 10 %, V _{IN} = 0.4 V or 1.6 V $^{\rm e}$		MIN. ^b	TYP. °	MAX. ^b	
Analog Switch			-		1	1	
Analog signal range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0	-	V+	V
On-resistance	R _{ON}	V+ = 1.8 V, V_{COM} = 0.2 V / 0.9 V I _{NO} , I _{NC} = 10 mA	Room Full ^d	-	5	10 15	
R _{ON} flatness ^d	R _{ON} flatness	$V_{+} = 1.8 V, V_{COM} = 0 V to V_{+},$	Room	-	6	9	Ω
R _{ON} match ^d	ΔR_{ON}	I_{NO} , $I_{NC} = 10 \text{ mA}$	Room	-	-	0.3	
	I _{NO(off)}		Room	-0.5	-	0.5	
Quitals off looks as a survey of f	I _{NC(off)}	V + = 2.2 V	Full	-5	-	5	
Switch off leakage current f		V _{NO} , V _{NC} = 0.5 V / 1.5 V, V _{COM} = 1.5 V / 0.5 V	Room	-0.5	-	0.5	- 1
	I _{COM(off)}		Full ^d	-5	-	5	nA
Channel-on leakage current f		V+ = 2.2 V,	Room	-0.5	-	0.5	
Channel-on leakage current	I _{COM(on)}	$V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Full ^d	-5	-	5	
Digital Control							
Input high voltage	V _{INH}		Full	1.6	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.4	v
Input capacitance ^d	CIN		Full	-	3	-	pF
Input current ^f	$I_{\rm INL}$ or $I_{\rm INH}$	$V_{IN} = 0 V \text{ or } V+$	Full	-1	-	1	μA
Dynamic Characteristics							
Turn-on time ^d	t _{on}		Room	-	37	57	ns
	UN	$\lambda = 15 \lambda$	Full ^d	-	-	60	
Turn-off time ^d	t _{OFF}	V _{NO} or V _{NC} = 1.5 V, R _I = 300 Ω, C _I = 35 pF	Room	-	26	44	
	OFF		Full ^d	-	-	45	
Break-before-make time ^d	t _d		Room	1	17	-	
Charge injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room	-	21	-	рС
Off-isolation ^d	OIRR	$R_{L} = 50 \Omega$, $C_{L} = 5 pF$, f = 1 MHz	Room	-	-63	-	dB
Crosstalk ^d	X _{TALK}		Room	-	-63	-	
N_O , N_C off capacitance ^d	C _{NO(off)} C _{NC(off)}	$V_{IN} = 0 V \text{ or } V+, f = 1 MHz$	Room	-	16	-	pF
Channel-on capacitance ^d	C _{ON}		Room	-	- 51 -		
Power Supply			-				
Power supply current	l+	$V_{IN} = 0 V \text{ or } V+$	Full	-	0.00001	1	μA

Notes

a. Room = 25 °C, full = as determined by the operating suffix

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

c. Typical values are for design aid only, not guaranteed nor subject to production testing

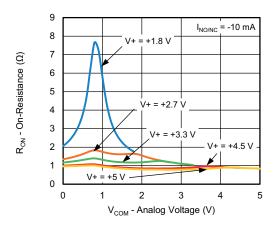
d. Guarantee by design, nor subjected to production test

e. V_{IN} = input voltage to perform proper function

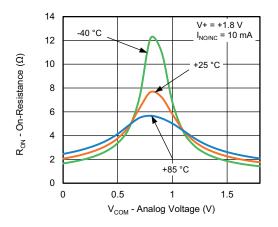
f. Guaranteed by 5 V leakage testing, not production tested



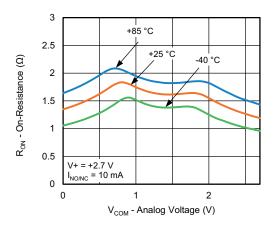
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



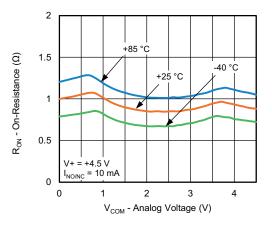
R_{ON} vs. V_{COM} and Supply Voltage



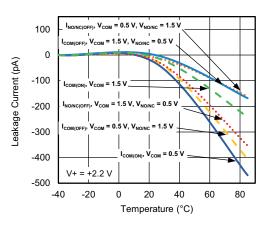
R_{ON} vs. V_{COM} and Temperature



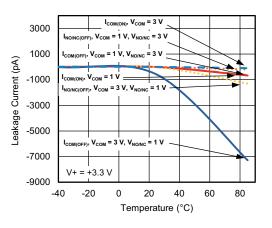
 R_{ON} vs. V_{COM} and Temperature



 R_{ON} vs. V_{COM} and Temperature



Leakage Current vs. Temperature



Leakage Current vs. Temperature

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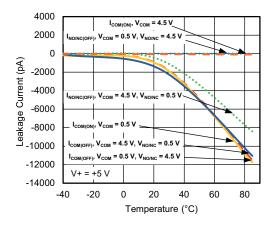
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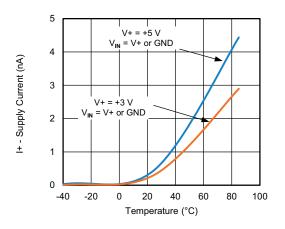
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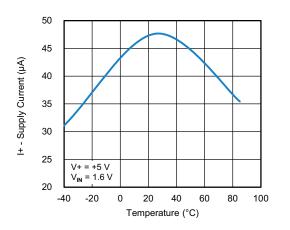
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



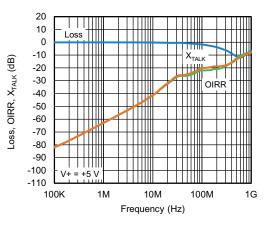
Leakage Current vs. Temperature



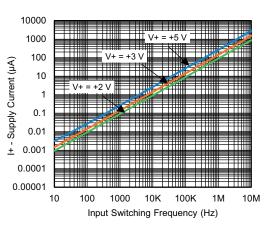
Supply Current vs. Temperature



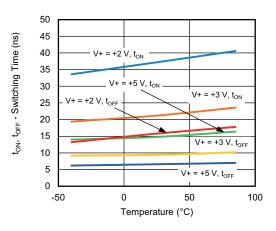
Supply Current vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency



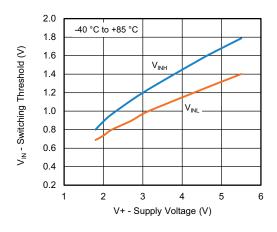
Supply Current vs. Input Switching Frequency



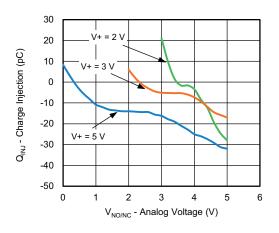
Switching Time vs. Temperature and Supply Voltage



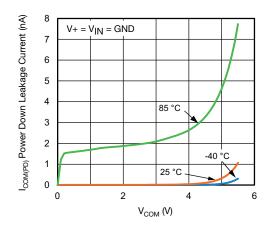
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



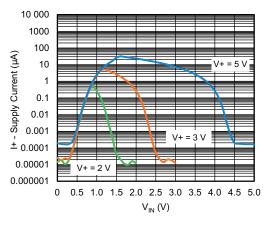
Switching Threshold vs. Supply Voltage



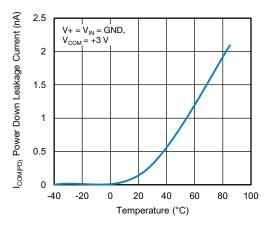
Charge Injection vs. Analog Voltage



Power Down Leakage Current vs. V_{COM}



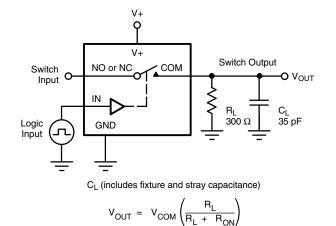
Supply Current vs. Enable Input Voltage

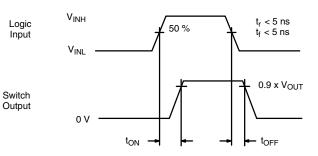


Power Down Leakage Current vs. Temperature



TEST CIRCUITS

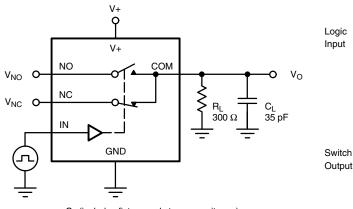




Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



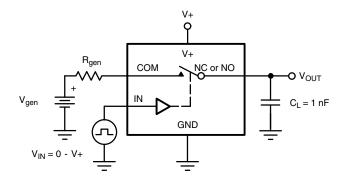
VINH

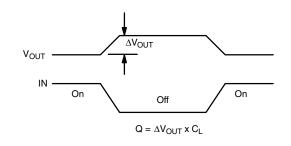


t_r < 5 ns t_f < 5 ns V_{INL} $V_{NC} = V_{NO}$ Vo 90 % 0 V t_D t_D

CL (includes fixture and stray capacitance)

Fig. 2 - Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 3 - Charge Injection

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TEST CIRCUITS

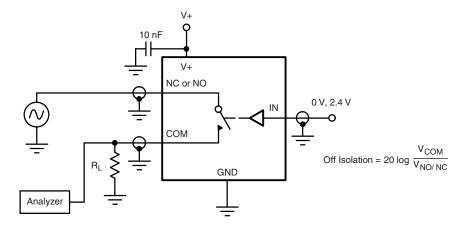


Fig. 4 - Off-Isolation

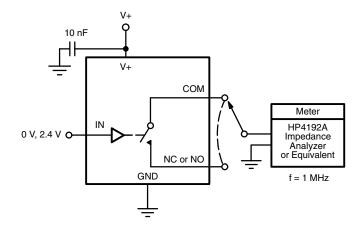


Fig. 5 - Channel Off / On Capacitance

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